

# Ultra-Small Footprint P-Channel FemtoFET™ MOSFET Test EVM

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## 1 Introduction

The evaluation module (EVM) CSD1FPCHEVM-890 provides the test interface for the following P-channel FemtoFETs: CSD23280F3, CSD23382F4, CSD23285F5, CSD25480F3, CSD25481F4, and CSD25485F5.

# 2 Description

The CSD1FPCHEVM-890 is designed to test six P-Channel FemtoFETs. For each MOSFET, the Drain, Gate, and Source terminals can be connected to customer test circuit through the headers for device and system evaluation. The EVM also provides sense points to evaluate the performance of the MOSFETs.



# 3 Electrical Performance Specifications

Table 1. CSD1FPCHEVM-890 Electrical Performance Specifications

PARAMETER	DESCRIPTION	MIN	TYP MAX	UNITS			
CSD23280F3							
Input Characteristics							
V <sub>DS</sub>	Drain-to-Source Voltage		-12	V			
V <sub>GS</sub>	Gate-to-Source Voltage		-6	٧			
Output Characteristics							
I <sub>D</sub> <sup>(1)</sup>	Continuous Drain Current, Max Cu		-3.0	Α			
I <sub>D</sub> <sup>(1)</sup>	Continuous Drain Current, Min Cu		-1.8	Α			
I <sub>DM</sub> (2)	Pulsed Drain Current		-11.4	Α			
CSD23382F4							
Input Characteristics							
V <sub>DS</sub>	Drain-to-Source Voltage		-12	V			
V <sub>GS</sub>	Gate-to-Source Voltage		±8	V			
Output Characteristics		-					
I <sub>D</sub> <sup>(1)</sup>	Continuous Drain Current, Max Cu		-3.5	Α			
I <sub>D</sub> <sup>(1)</sup>	Continuous Drain Current, Min Cu		-2.3	Α			
I <sub>DM</sub> <sup>(2)</sup>	Pulsed Drain Current		-14.4	Α			
CSD23285F5		*		I			
Input Characteristics							
V <sub>DS</sub>	Drain-to-Source Voltage		-12	V			
V <sub>GS</sub>	Gate-to-Source Voltage		-6	V			
Output Characteristics		*		I.			
I <sub>D</sub> <sup>(1)</sup>	Continuous Drain Current, Max Cu		-5.4	Α			
I <sub>D</sub> <sup>(1)</sup>	Continuous Drain Current, Min Cu		-3.3	Α			
I <sub>DM</sub> <sup>(2)</sup>	Pulsed Drain Current		-31				
CSD25480F3		*					
Input Characteristics							
V <sub>DS</sub>	Drain-to-Source Voltage		-20	V			
V <sub>GS</sub>	Gate-to-Source Voltage		-12	V			
Output Characteristics							
I <sub>D</sub> <sup>(1)</sup>	Continuous Drain Current, Max Cu		-2.8	Α			
I <sub>D</sub> <sup>(1)</sup>	Continuous Drain Current, Min Cu		-1.7	Α			
I <sub>DM</sub> <sup>(2)</sup>	Pulsed Drain Current		-10.6	Α			
CSD25481F4							
Input Characteristics							
V <sub>DS</sub>	Drain-to-Source Voltage		-20	V			
V <sub>GS</sub>	Gate-to-Source Voltage		-12	V			
<b>Output Characteristics</b>							
I <sub>D</sub> <sup>(1)</sup>	Continuous Drain Current, Max Cu		-2.5	Α			
I <sub>D</sub> <sup>(1)</sup>	Continuous Drain Current, Min Cu		-2.1	Α			
I <sub>DM</sub> (2)	Pulsed Drain Current		-13.1	Α			
CSD25485F5							
Input Characteristics							
V <sub>DS</sub>	Drain-to-Source Voltage		-20	V			
V <sub>GS</sub>	Gate-to-Source Voltage		-12	V			
	+						

<sup>(1)</sup> Refer to the thermal values in the respective data sheets.

<sup>&</sup>lt;sup>(2)</sup> Pulse duration ≤ 100 μs, duty cycle ≤ 1%.



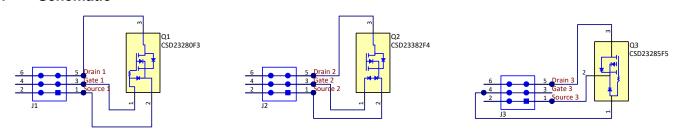
# Table 1. CSD1FPCHEVM-890 Electrical Performance Specifications (continued)

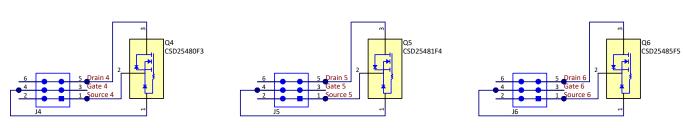
PARAMETER	DESCRIPTION	MIN	TYP	MAX	UNITS		
Output Characteristics							
I <sub>D</sub> <sup>(1)</sup>	Continuous Drain Current, Max Cu			-5.3	Α		
I <sub>D</sub> <sup>(1)</sup>	Continuous Drain Current, Min Cu			-3.3	Α		
I <sub>DM</sub> <sup>(2)</sup>	Pulsed Drain Current			-31	Α		



Schematic www.ti.com

## 4 Schematic





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Figure 1. CSD1FPCHEVM-890 Schematic



www.ti.com Test Setup

## 5 Test Setup

#### 5.1 Board Picture

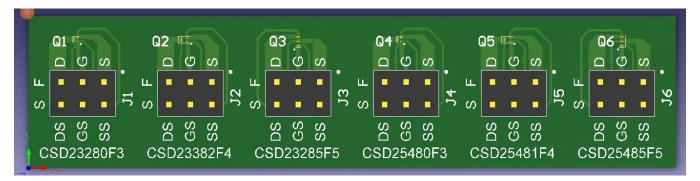
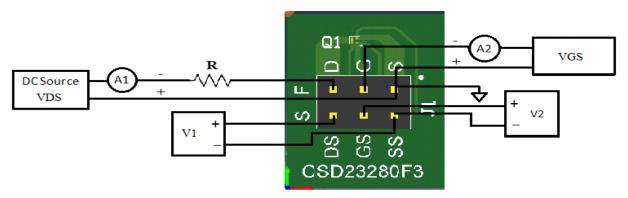


Figure 2. CSD1FPCHEVM-890

Figure 2 is board picture of the CSD1FPCHEVM-890. For each MOSFET, there is a connector which provides the force and sense points to the Drain, Gate, and, Source terminals. The D (Drain), G (Gate), and S (Source) are the force points which need to be connected to the test circuit; while DS (Drain Sense), GS (Gate Sense), and SS (Source Sense) are the sense points which can be used to measure the voltages.

#### 5.1.1 Test Set-Up Example



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Figure 3. CSD1FPCHEVM-890

Figure 3 shows an example of the test setup for CSD23280F3: a voltage source  $V_{DS}$  is connected to D and S through a load resistor and a voltage source  $V_{GS}$  is connected to the G and S. With  $V_{DS}$  voltage being applied, the MOSFET will be turned on if  $V_{GS}$  is smaller than the threshold voltage. V1 and V2 are the voltage meters to measure the  $V_{DS}$  and  $V_{GS}$  voltages, while A1 and A2 are the current meters to monitor the currents  $I_D$  and  $I_G$ .

Table 1 lists the maximum V<sub>GS</sub> and V<sub>DS</sub> voltages and maximum I<sub>D</sub> current for each of the devices.



## 6 EVM Assembly Drawing and PCB Layout

The following figures (Figure 4 and Figure 5) show the design of the CSD1FPCHEVM-890 printed circuit board. The EVM has been designed using a 2-Layer circuit board.

## 6.1 Top Layer Assembly Drawing (Top View)

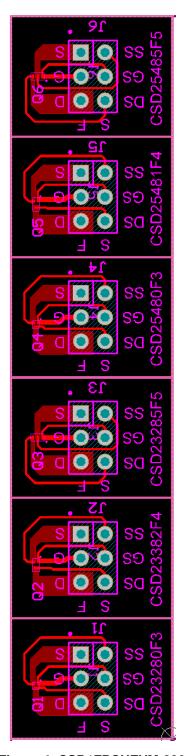


Figure 4. CSD1FPCHEVM-890



# 6.2 Bottom Assembly Drawing (Bottom View)

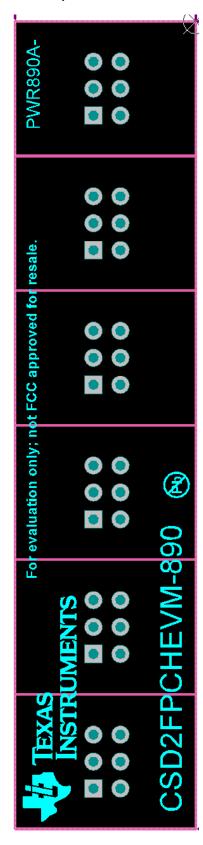


Figure 5. CSD1FPCHEVM-890



Bill of Materials www.ti.com

# 7 Bill of Materials

The EVM components list according to the schematic in Figure 1.

**Table 2. List of Materials** 

PART NUMBER	DESCRIPTION	DESIGNATOR	FOOTPRINT	LIB REF	QTY
PWR890	Printed Circuit Board	PCB1		PCB	1
TSW-103-07-G-D	Header, 100 mil, 3×2, Gold, TH	J1, J2, J3, J4, J5, J6	TSW-103-07-G-D	TSW-103-07-G-D	6
CSD23280F3	12-V P-Ch FemtoFET	Q1	FemtoF3	CSD23280F3	1
CSD23382F4	12-V P-Ch FemtoFET	Q2	FemtoF4	CSD23382F4	1
CSD23385F5	12-V P-Ch FemtoFET	Q3	FemtoF5	CSD23385F5	1
CSD25480F3	20-V P-Ch FemtoFET	Q4	FemtoF3	CSD25480F3	1
CSD25481F4	20-V P-Ch FemtoFET	Q5	FemtoF4	CSD25481F4	1
CSD25485F5	20-V P-Ch FemtoFET	Q6	FemtoF5	CSD25485F5	1

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## **EVM Warnings and Restrictions**

It is important to operate this EVM within the input voltage range of and the output voltage range of .

Exceeding the specified input range may cause unexpected operation and/or irreversible damage to the EVM. If there are questions concerning the input range, please contact a TI field representative prior to connecting the input power.

Applying loads outside of the specified output range may result in unintended operation and/or possible permanent damage to the EVM. Please consult the EVM User's Guide prior to connecting any load to the EVM output. If there is uncertainty as to the load specification, please contact a TI field representative.

During normal operation, some circuit components may have case temperatures greater than. The EVM is designed to operate properly with certain components above as long as the input and output ranges are maintained. These components include but are not limited to linear regulators, switching transistors, pass transistors, and current sense resistors. These types of devices can be identified using the EVM schematic located in the EVM User's Guide. When placing measurement probes near these devices during operation, please be aware that these devices may be very warm to the touch.

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